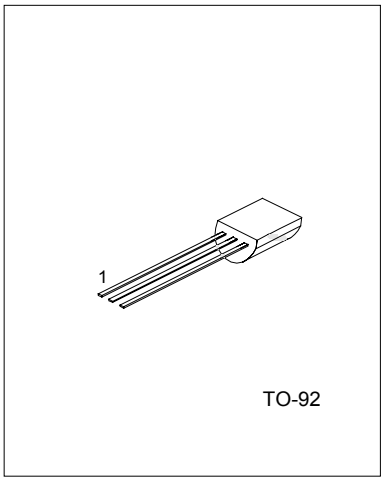
UTC 2SD468 NPN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER



TO-92

1:EMITTER 2:COLLECTOR 3:BASE

FEATURES

*Low frequency power amplifier

*Complement to 2SB562

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	25	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	Ic	1	A
Collector Peak Current	Ic(peak)	1.5	A
Collector Power Dissipation	P_C	0.9	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

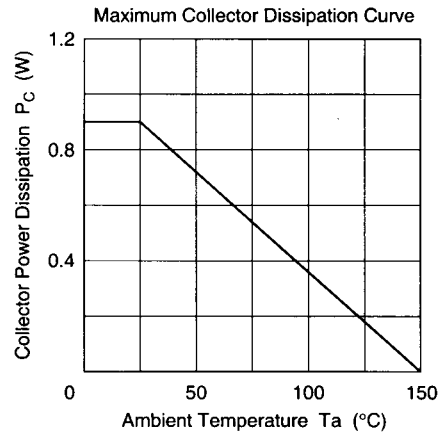
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector to base breakdown voltage	$V_{(BR)CBO}$	I_C=10μA, I_E=0	25			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	Ic=1mA, R_{BE}=∞	20			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0	5			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=20V, I_E=0			1	μA
DC Current transfer ratio	h_{FE}	V_{CE}=2V, Ic=0.5A (note)	85		240	
Collector to emitter saturation voltage	V_{CE}(sat)	Ic=0.8A, I_B=0.08A (note)		0.2	0.5	V
Base to emitter voltage	V_{BE}	V_{CE}=2V, Ic=0.5A (note)		0.79	1	V
Gain bandwidth product	f_T	V_{CE}=2V, Ic=0.5A (note)		190		MHz
Collector output capacitance	Cob	V_{CB}=10V, I_E=0, f=1MHz		22		pF

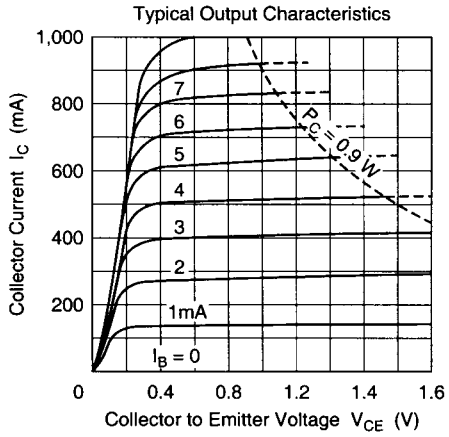
Note: Pulse test

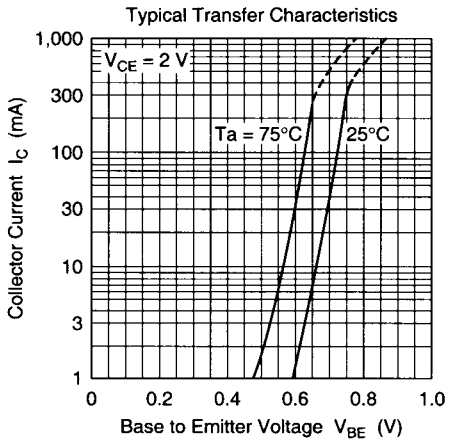
CLASSIFICATION OF h_{FE}

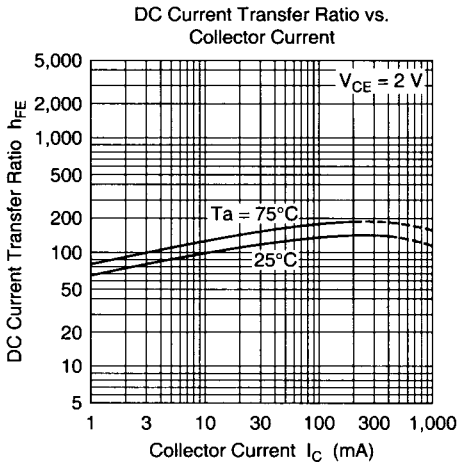
RANK	B	C
RANGE	85 - 170	120 - 240

TYPICAL PERFORMANCE CHARACTERISTICS

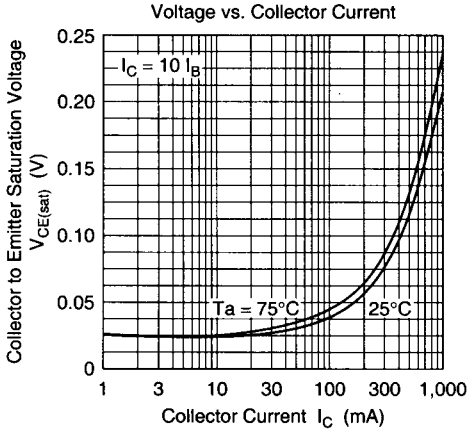




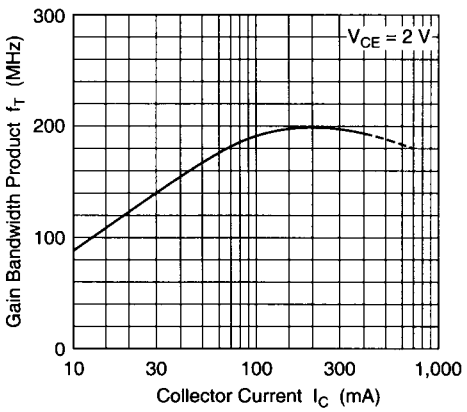




Collector to Emitter Saturation Voltage vs. Collector Current



Gain Bandwidth Product vs. Collector Current



Collector Output Capacitance vs. Collector to Base Voltage